

ABSTRACT

A ruthenium sputtering target, wherein a Si content is 10 to 100 wtppm, a total content of unavoidable impurities excluding gas components is 50 wtppm or less, and a remainder is Ru. By suppressing the crystal growth of ruthenium or a ruthenium alloy and reducing the generation of coarse crystal grains, arcing that occurs during sputtering is minimized, particle generation is reduced, and yield is improved.